



**12NM90**

Preliminary

**Power MOSFET**

**12A, 900V N-CHANNEL SUPER-JUNCTION MOSFET**

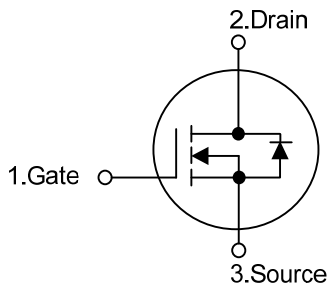
■ DESCRIPTION

The **UTC 12NM90** is a Super Junction MOSFET Structure and is designed to have better characteristics, such as fast switching time, low gate charge, low on-state resistance and a high rugged avalanche characteristics. This power MOSFET is usually used at DC-DC, AC-DC converters for power applications.

■ FEATURES

- \*  $R_{DS(ON)} < 0.7\Omega @ V_{GS} = 10V, I_D = 6.0A$
- \* Fast switching capability
- \* Avalanche energy tested
- \* Improved dv/dt capability, high ruggedness

■ SYMBOL

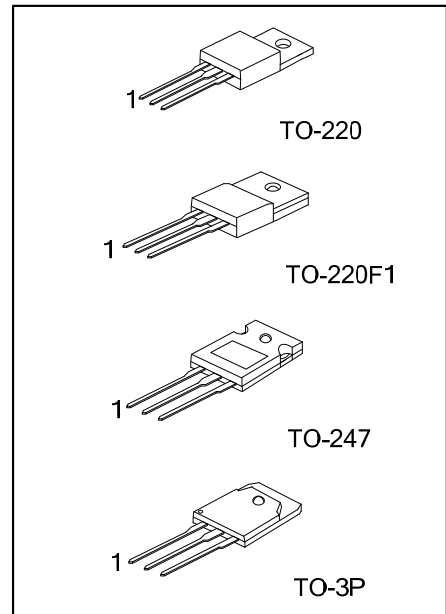


■ ORDERING INFORMATION

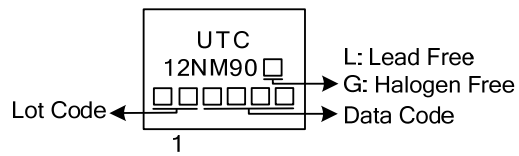
Ordering Number		Package	Pin Assignment			Packing
Lead Free	Halogen Free		1	2	3	
12NM90L-TA3-T	12NM90G-TA3-T	TO-220	G	D	S	Tube
12NM90L-TF1-T	12NM90G-TF1-T	TO-220F1	G	D	S	Tube
12NM90L-T47-T	12NM90G-T47-T	TO-247	G	D	S	Tube
12NM90L-T3P-T	12NM90G-T3P-T	TO-3P	G	D	S	Tube

Note: Pin Assignment: G: Gate D: Drain S: Source

<p>12NM90L-TA3-T</p> <p>(1)Packing Type (2)Package Type (3)Green Package</p>	<p>(1) T: Tube (2) TA3: TO-220, TF1: TO-220F1, T3P: TO-3P T47: TO-247 (3) L: Lead Free, G: Halogen Free and Lead Free</p>
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### MARKING



■ ABSOLUTE MAXIMUM RATINGS ( $T_C = 25^\circ\text{C}$ , unless otherwise specified)

PARAMETER		SYMBOL	RATINGS	UNIT
Drain-Source Voltage		$V_{DSS}$	900	V
Gate-Source Voltage		$V_{GSS}$	$\pm 30$	V
Continuous Drain Current	Continuous	$I_D$	12	A
Pulsed Drain Current	Pulsed (Note 2)	$I_{DM}$	48	A
Avalanche Current (Note 2)		$I_{AR}$	2.8	A
Single Pulsed Avalanche Energy	Single Pulsed (Note 3)	$E_{AS}$	623	mJ
Peak Diode Recovery dv/dt (Note 4)		dv/dt	2.4	V/ns
Power Dissipation	TO-220	$P_D$	180	W
	TO-220F1		51	W
	TO-3P		390	W
	TO-247		360	W
Junction Temperature		$T_J$	+150	$^\circ\text{C}$
Storage Temperature		$T_{STG}$	-55 ~ +150	$^\circ\text{C}$

Notes: 1. Absolute maximum ratings are those values beyond which the device could be permanently damaged.

Absolute maximum ratings are stress ratings only and functional device operation is not implied.

2. Repetitive Rating: Pulse width limited by maximum junction temperature.

3.  $L = 159\text{mH}$ ,  $I_{AS} = 2.8\text{A}$ ,  $V_{DD} = 50\text{V}$ ,  $R_G = 25\Omega$ , Starting  $T_J = 25^\circ\text{C}$ .

4.  $I_{SD} \leq 12\text{A}$ ,  $di/dt \leq 200\text{A}/\mu\text{s}$ ,  $V_{DD} \leq BV_{DSS}$ , Starting  $T_J = 25^\circ\text{C}$ .

■ THERMAL DATA

PARAMETER		SYMBOL	RATINGS	UNIT
Junction to Ambient	TO-220/TO-220F1	$\theta_{JA}$	62.5	$^\circ\text{C}/\text{W}$
	TO-3P		30	$^\circ\text{C}/\text{W}$
	TO-247		40	$^\circ\text{C}/\text{W}$
Junction to Case	TO-220	$\theta_{JC}$	0.69	$^\circ\text{C}/\text{W}$
	TO-220F1		2.45	$^\circ\text{C}/\text{W}$
	TO-3P		0.32	$^\circ\text{C}/\text{W}$
	TO-247		0.35	$^\circ\text{C}/\text{W}$

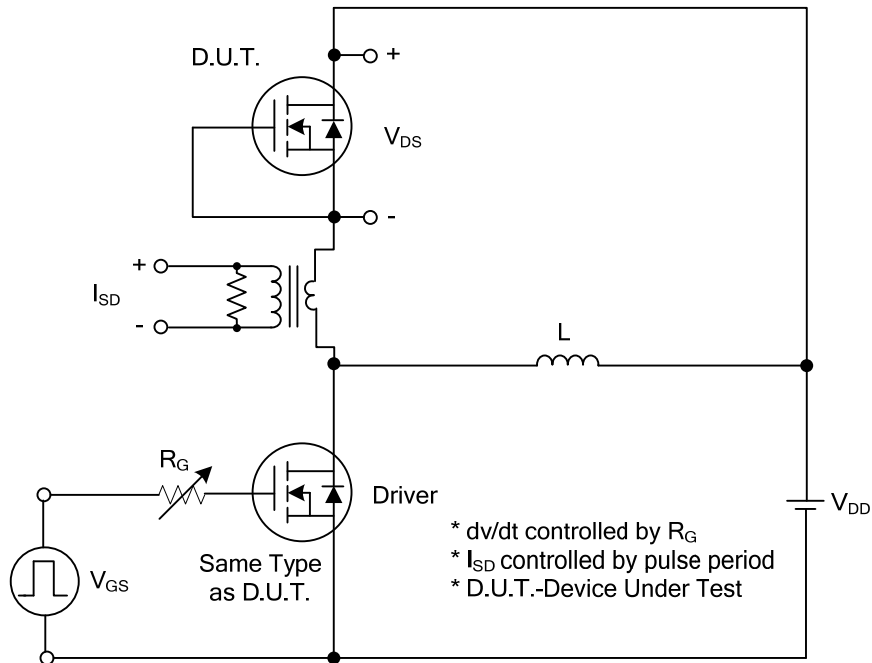
■ ELECTRICAL CHARACTERISTICS (T<sub>J</sub>=25°C, unless otherwise specified)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
<b>OFF CHARACTERISTICS</b>						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	V <sub>GS</sub> = 0V, I <sub>D</sub> = 250μA	900			V
Drain-Source Leakage Current	I <sub>DSS</sub>	V <sub>DS</sub> = 900V, V <sub>GS</sub> = 0V			10	μA
Gate-Source Leakage Current	Forward	I <sub>GSS</sub>			100	nA
	Reverse					
		V <sub>GS</sub> = -30V, V <sub>DS</sub> = 0V			-100	nA
<b>ON CHARACTERISTICS</b>						
Gate Threshold Voltage	V <sub>GS(TH)</sub>	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250μA	2.5		4.5	V
Static Drain-Source On-State Resistance	R <sub>DS(ON)</sub>	V <sub>GS</sub> = 10V, I <sub>D</sub> = 6.0A			0.7	Ω
<b>DYNAMIC CHARACTERISTICS</b>						
Input Capacitance	C <sub>ISS</sub>	V <sub>GS</sub> =0V, V <sub>DS</sub> =25V, f=1.0MHz		1230		pF
Output Capacitance	C <sub>OSS</sub>			425		pF
Reverse Transfer Capacitance	C <sub>RSS</sub>			9		pF
<b>SWITCHING CHARACTERISTICS</b>						
Total Gate Charge (Note 1)	Q <sub>G</sub>	V <sub>DS</sub> =50V, I <sub>D</sub> =1.3A, I <sub>G</sub> =100μA V <sub>GS</sub> =10V (Note 1,2)		65		nC
Gate to Source Charge	Q <sub>GS</sub>			6		nC
Gate to Drain Charge	Q <sub>GD</sub>			21		nC
Turn-ON Delay Time (Note 1)	t <sub>D(ON)</sub>	V <sub>DD</sub> =30V, I <sub>D</sub> =0.5A, R <sub>G</sub> =25Ω, V <sub>GS</sub> =10V (Note 1,2)		58		nS
Rise Time	t <sub>R</sub>			125		nS
Turn-OFF Delay Time	t <sub>D(OFF)</sub>			500		nS
Fall-Time	t <sub>F</sub>			135		nS
<b>SOURCE- DRAIN DIODE RATINGS AND CHARACTERISTICS</b>						
Maximum Body-Diode Continuous Current	I <sub>S</sub>				12	A
Maximum Body-Diode Pulsed Current	I <sub>SM</sub>				48	A
Drain-Source Diode Forward Voltage (Note 1)	V <sub>SD</sub>	I <sub>S</sub> =12A, V <sub>GS</sub> =0V			1.4	V
Body Diode Reverse Recovery Time (Note 1)	t <sub>rr</sub>	I <sub>S</sub> =12A, V <sub>GS</sub> =0V, dI <sub>F</sub> /dt=100A/μs		595		nS
Body Diode Reverse Recovery Charge	Q <sub>rr</sub>				10.4	

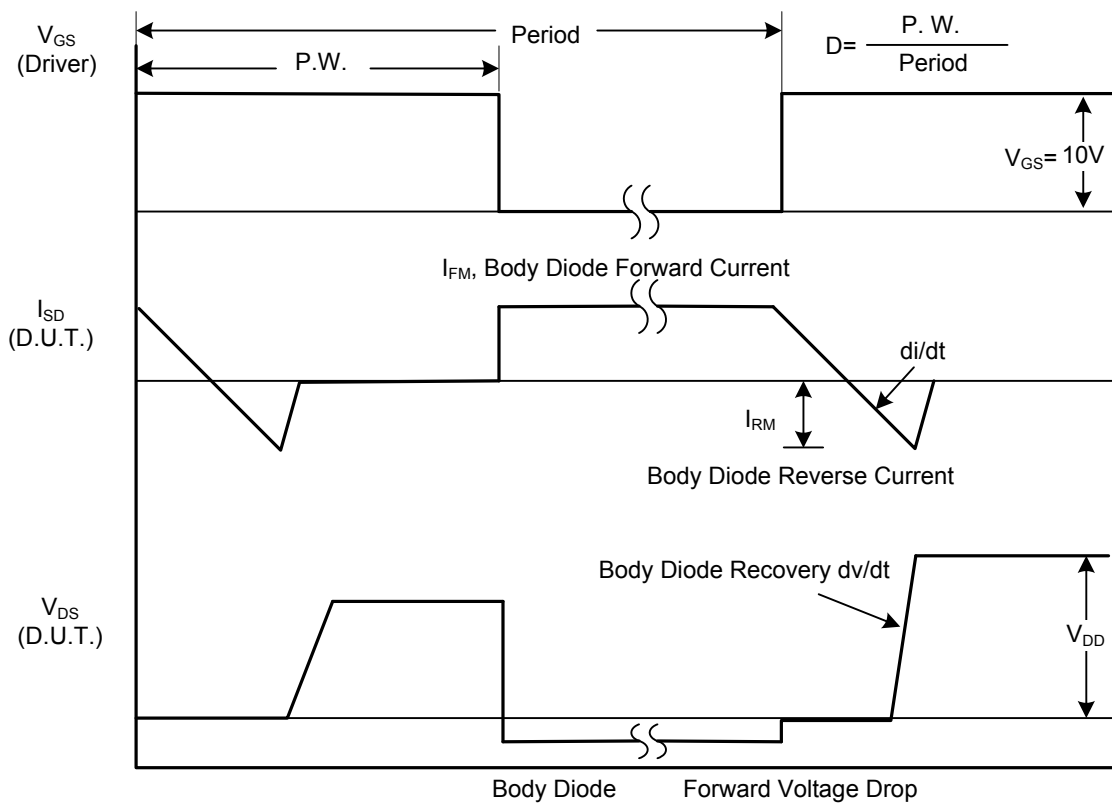
Notes: 1. Pulse Test : Pulse width ≤ 300μs, Duty cycle ≤ 2%.

2. Essentially independent of operating ambient temperature.

■ TEST CIRCUITS AND WAVEFORMS

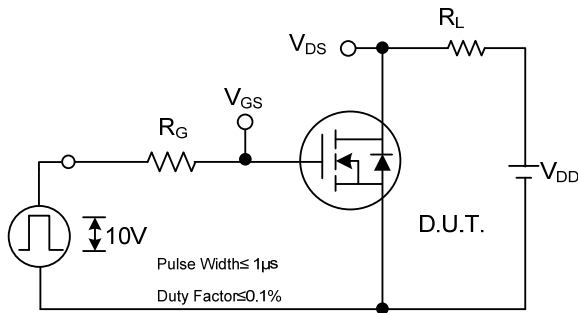


Peak Diode Recovery dv/dt Test Circuit

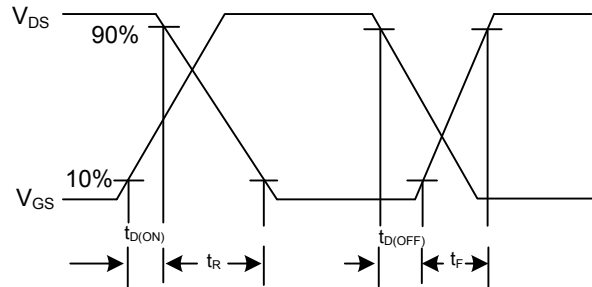


Peak Diode Recovery dv/dt Waveforms

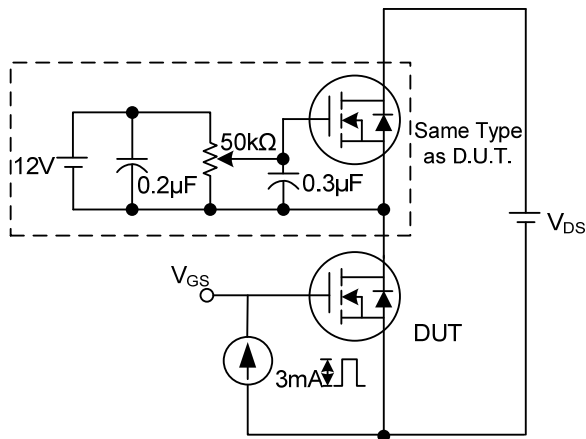
■ TEST CIRCUITS AND WAVEFORMS (Cont.)



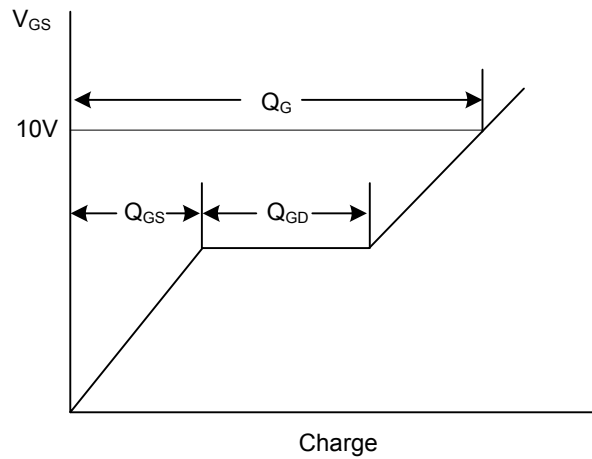
Switching Test Circuit



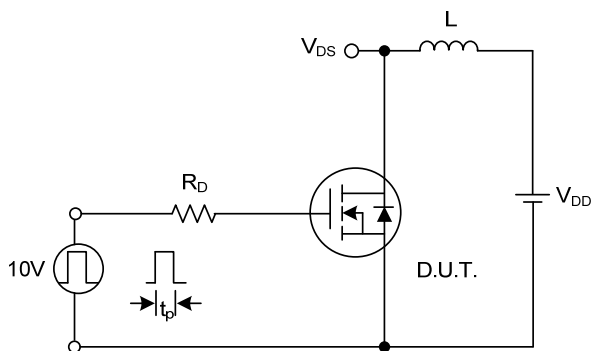
Switching Waveforms



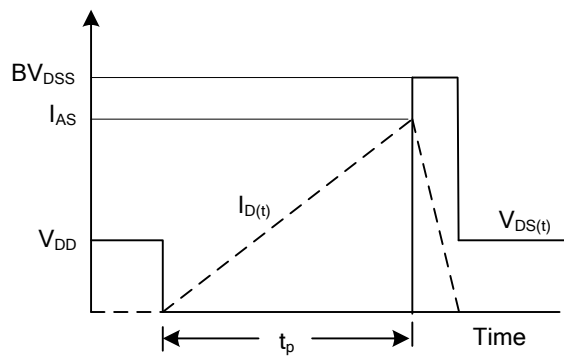
Gate Charge Test Circuit



Gate Charge Waveform



Unclamped Inductive Switching Test Circuit



Unclamped Inductive Switching Waveforms

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